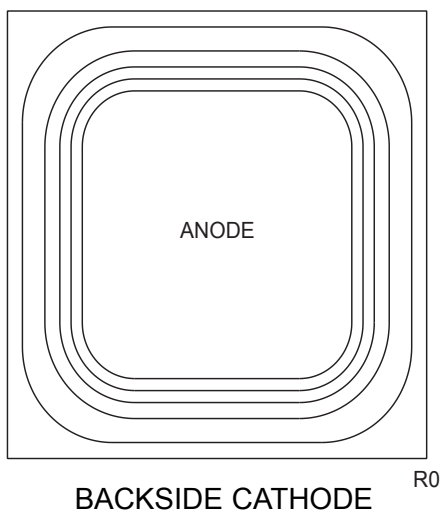


PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	33.5 X 33.5 MILS
Die Thickness	8.0 MILS
Anode Bonding Pad Area	23 X 23 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



GROSS DIE PER 4 INCH WAFER

10,070

PRINCIPAL DEVICE TYPES

1N5913B
THRU
1N5956B

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